

EN: This Datasheet is presented by the manufacturer.

Please visit our website for pricing and availability at www.hestore.hu.



MCP1403/4/5

4.5A Dual High-Speed Power MOSFET Drivers

Features

- High Peak Output Current: 4.5A (typ.)
- Low Shoot-Through/Cross-Conduction Current in Output Stage
- · Wide Input Supply Voltage Operating Range:
 - 4.5V to 18V
- · High Capacitive Load Drive Capability:
 - 2200 pF in 15 ns
 - 5600 pF in 34 ns
- · Short Delay Times: 40 ns (typ.)
- · Low Supply Current:
 - With Logic '1' Input 1.0 mA (typ.)
 - With Logic '0' Input 150 μA (typ.)
- Latch-Up Protected: Will Withstand 1.5A Reverse Current
- Logic Input Will Withstand Negative Swing Up To 5V
- Packages: 8-Pin SOIC, PDIP, 8-Pin 6x5 DFN, and 16-Pin SOIC

Applications

- · Switch Mode Power Supplies
- · Pulse Transformer Drive
- · Line Drivers
- · Motor and Solenoid Drive

General Description

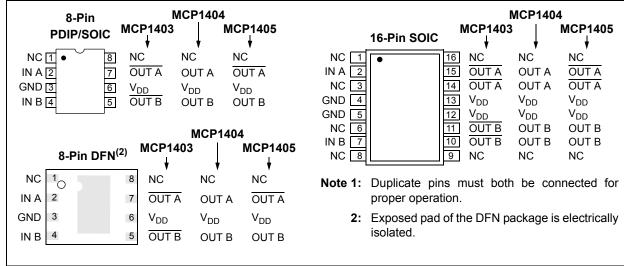
The MCP1403/4/5 are a family of dual-inverting, dual-non-inverting, or complimentary output drivers. They can delivery high peak currents of 4.5A typically into capacitive loads. These devices also feature low shoot-through current, matched rise/fall times and propagation delays.

The MCP1403/4/5 drivers operate from a 4.5V to 18V single power supply and can easily charge and discharge 2200 pF gate capacitance in under 15 ns (typ). They provide low enough impedances in both the on and off states to ensure the MOSFETs intended state will not be affected, even by large transients. The input to the MCP1403/4/5 may be driven directly from either TTL or CMOS (3V to 18V).

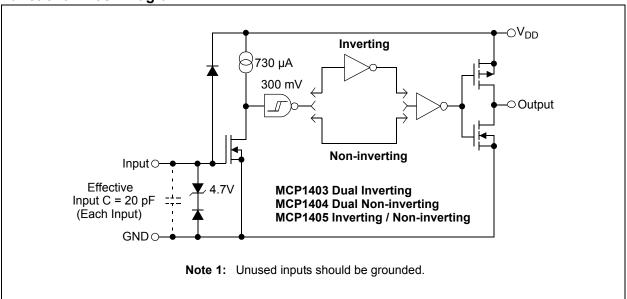
The MCP1403/4/5 dual-output 4.5A driver family is offered in both surface-mount and pin-through-hole packages with a -40°C to +125°C temperature rating. The low thermal resistance of the thermally enhanced DFN package allows for greater power dissipation capability for driving heavier capacitive or resistive loads.

These devices are highly latch-up resistant under any conditions within their power and voltage ratings. They are not subject to damage when up to 5V of noise spiking (of either polarity) occurs on the ground pin. All terminals are fully protect against Electrostatic Discharge (ESD) up to 4 kV.

Package Types



Functional Block Diagram ⁽¹⁾



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings †

Supply Voltage	+20V
Input Voltage	(V _{DD} + 0.3V) to (GND – 5V)
Input Current (V _{IN} >V _{DD})	50 mA

† **Notice:** Stresses above those listed under "Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS (NOTE 2)

Electrical Specifications: Unless otherwise indicated, $T_A = +25^{\circ}C$, with $4.5V \le V_{DD} \le 18V$.							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Input							
Logic '1', High Input Voltage	V _{IH}	2.4	1.5	_	V		
Logic '0', Low Input Voltage	V_{IL}	_	1.3	0.8	V		
Input Current	I _{IN}	-1	_	1	μΑ	$0V \le V_{IN} \le V_{DD}$	
Input Voltage	V _{IN}	-5	_	V _{DD} +0.3	V		
Output							
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	_	V	DC Test	
Low Output Voltage	V _{OL}	_	_	0.025	V	DC Test	
Output Resistance, High	R _{OH}	_	2.2	3.0	Ω	I _{OUT} = 10 mA, V _{DD} = 18V	
Output Resistance, Low	R _{OL}	_	2.8	3.5	Ω	I _{OUT} = 10 mA, V _{DD} = 18V	
Peak Output Current	I _{PK}	_	4.5	_	Α	V _{DD} = 18V (Note 2)	
Latch-Up Protection Withstand Reverse Current	I _{REV}	_	>1.5	_	Α	Duty cycle \leq 2%, t \leq 300 µsec.	
Switching Time (Note 1)	•			•			
Rise Time	t _R	_	15	28	ns	Figure 4-1, Figure 4-2 C _L = 2200 pF	
Fall Time	t _F	_	18	28	ns	Figure 4-1, Figure 4-2 C _L = 2200 pF	
Delay Time	t _{D1}	_	40	48	ns	Figure 4-1, Figure 4-2	
Delay Time	t _{D2}	_	40	48	ns	Figure 4-1, Figure 4-2	
Power Supply							
Supply Voltage	V_{DD}	4.5	_	18.0	V		
Power Supply Current	I _S	_	1.0	2.0	mA	V _{IN} = 3V (Both Inputs)	
	I _S	_	0.15	0.25	mA	V _{IN} = 0V (Both Inputs)	

Note 1: Switching times ensured by design.

^{2:} Tested during characterization, not production tested.

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise indicated, operating temperature range with $4.5V \le V_{DD} \le 18V$.								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
Input								
Logic '1', High Input Voltage	V_{IH}	2.4	_	_	V			
Logic '0', Low Input Voltage	V_{IL}	_	_	0.8	V			
Input Current	I _{IN}	-10	_	+10	μΑ	$0V \le V_{IN} \le V_{DD}$		
Output								
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	_	V	DC TEST		
Low Output Voltage	V_{OL}	_	_	0.025	V	DC TEST		
Output Resistance, High	R _{OH}	_	3.1	6.0	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Output Resistance, Low	R _{OL}	_	3.7	7	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Switching Time (Note 1)								
Rise Time	t _R	_	25	40	ns	Figure 4-1, Figure 4-2 C _L = 2200 pF		
Fall Time	t _F	_	25	40	ns	Figure 4-1, Figure 4-2 C _L = 2200 pF		
Delay Time	t _{D1}	_	50	65	ns	Figure 4-1, Figure 4-2		
Delay Time	t _{D2}	_	50	65	ns	Figure 4-1, Figure 4-2		
Power Supply	Power Supply							
Power Supply Current	IS	_	2.0	3.0	mA	V _{IN} = 3V (Both Inputs)		
		_	0.2	0.3		V _{IN} = 0V (Both Inputs)		

Note 1: Switching times ensured by design.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with 4.5V \leq V _{DD} \leq 18V.									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Temperature Ranges									
Specified Temperature Range	T _A	-40	_	+125	°C				
Maximum Junction Temperature	TJ	_	_	+150	°C				
Storage Temperature Range	T _A	-65	_	+150	°C				
Package Thermal Resistances									
Thermal Resistance, 8L-6x5 DFN	$\theta_{\sf JA}$	_	33.2	_	°C/W	Typical four-layer board with vias to ground plane			
Thermal Resistance, 8L-PDIP	θ_{JA}	_	125	_	°C/W				
Thermal Resistance, 8L-SOIC	θ_{JA}	_	155	_	°C/W				
Thermal Resistance, 16L-SOIC	$\theta_{\sf JA}$	_	155	_	°C/W	4-Layer JC51-7 Standard Board, Natural Convection			

^{2:} Tested during characterization, not production tested.

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, T_A = +25°C with $4.5V \le V_{DD} \le 18V$.

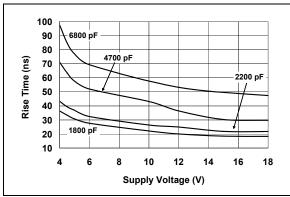


FIGURE 2-1: Rise Time vs. Supply Voltage.

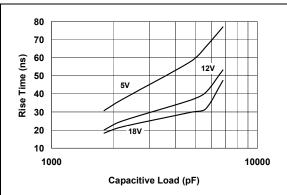


FIGURE 2-2: Rise Time vs. Capacitive Load.

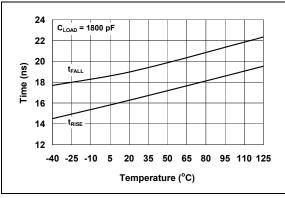


FIGURE 2-3: Rise and Fall Times vs. Temperature.

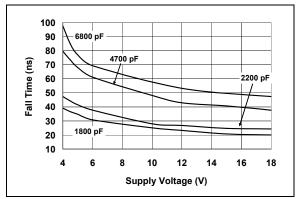


FIGURE 2-4: Fall Time vs. Supply Voltage.

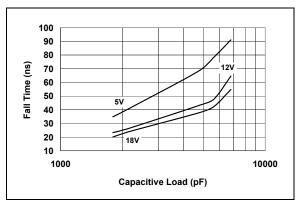


FIGURE 2-5: Fall Time vs. Capacitive Load.

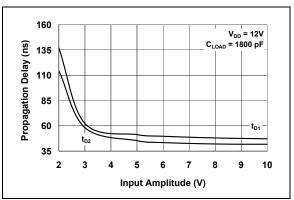


FIGURE 2-6: Propagation Delay vs. Input Amplitude.

Typical Performance Curves (Continued)

Note: Unless otherwise indicated, T_A = +25°C with 4.5V \leq V_{DD} \leq 18V.

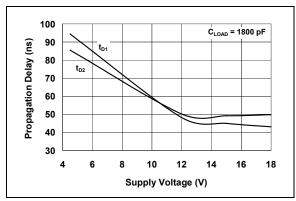


FIGURE 2-7: Propagation Delay Time vs. Supply Voltage.

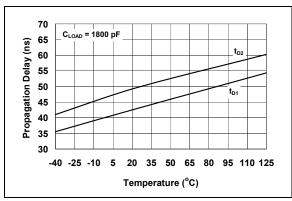


FIGURE 2-8: Propagation Delay Time vs. Temperature.

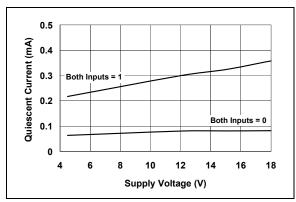


FIGURE 2-9: Quiescent Current vs. Supply Voltage.

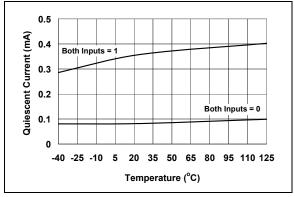


FIGURE 2-10: Quiescent Current vs. Temperature.

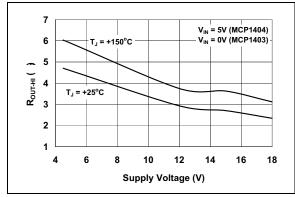


FIGURE 2-11: Output Resistance (Output High) vs. Supply Voltage.

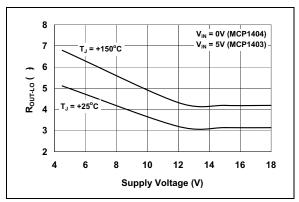


FIGURE 2-12: Output Resistance (Output Low) vs. Temperature.

Typical Performance Curves (Continued)

Note: Unless otherwise indicated, T_A = +25°C with $4.5V \le V_{DD} \le 18V$.

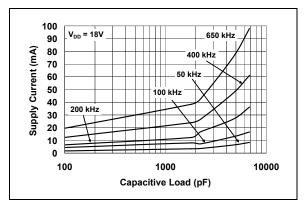


FIGURE 2-13: Supply Current vs. Capacitive Load.

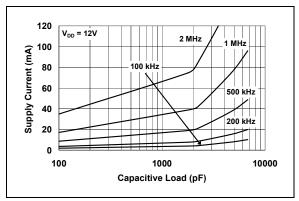


FIGURE 2-14: Supply Current vs. Capacitive Load.

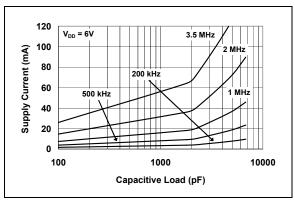


FIGURE 2-15: Supply Current vs. Capacitive Load.

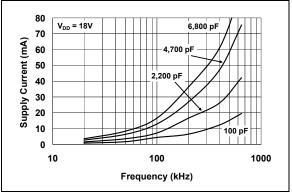


FIGURE 2-16: Supply Current vs. Frequency.

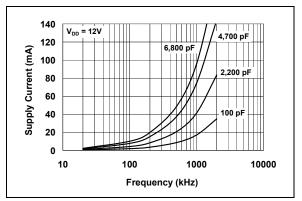


FIGURE 2-17: Supply Current vs. Frequency.

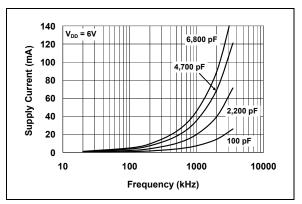


FIGURE 2-18: Supply Current vs. Frequency.

MCP1403/4/5

Typical Performance Curves (Continued)

Note: Unless otherwise indicated, T_A = +25°C with 4.5V \leq V_{DD} \leq 18V.

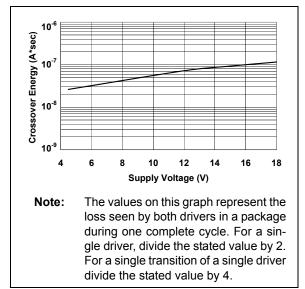


FIGURE 2-19: Crossover Energy vs. Supply Voltage.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE (1)

8-Pin PDIP SOIC	8-Pin DFN	16-Pin SOIC	Symbol	Description
1	1	1	NC	No Connection
2	2	2	IN A	Control Input for Output A
_	_	3	NC	No Connection
3	3	4	GND	Ground
_	_	5	GND	Ground
_	_	6	NC	No Connection
4	4	7	IN B	Control Input for Output B
_	_	8	NC	No Connection
_	_	9	NC	No Connection
5	5	10	OUT B	Output B
_	_	11	OUT B	Output B
6	6	12	V_{DD}	Supply Input
_	_	13	V_{DD}	Supply Input
7	7	14	OUT A	Output A
_	_	15	OUT A	Output A
8	8	16	NC	No Connection
_	PAD	_	NC	Exposed Metal Pad

Note 1: Duplicate pins must be connected for proper operation.

3.1 Supply Input (V_{DD})

 V_{DD} is the bias supply input for the MOSFET driver and has a voltage range of 4.5V to 18V. This input must be decoupled to ground with a local capacitor. This bypass capacitor provides a localized low-impedance path for the peak currents that are to be provided to the load.

3.2 Control Inputs A and B

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input also has hysteresis between the high and low input levels, allowing them to be driven from slow rising and falling signals, and to provide noise immunity.

3.3 Ground (GND)

Ground is the device return pin. The ground pin should have a low impedance connection to the bias supply source return. High peak currents will flow out the ground pin when the capacitive load is being discharged.

3.4 Outputs A and B

Outputs A and B are CMOS push-pull output that is capable of sourcing and sinking 4.5A of peak current (V_{DD} = 18V). The low output impedance ensures the gate of the external MOSFET will stay in the intended state even during large transients. These output also has a reverse current latch-up rating of 1.5A.

3.5 Exposed Metal Pad

The exposed metal pad of the DFN package is not internally connected to any potential. Therefore, this pad can be connected to a ground plane or other copper plane on a printed circuit board to aid in heat removal from the package.

4.0 APPLICATION INFORMATION

4.1 General Information

MOSFET drivers are high-speed, high current devices which are intended to source/sink high peak currents to charge/discharge the gate capacitance of external MOSFETs or IGBTs. In high frequency switching power supplies, the PWM controller may not have the drive capability to directly drive the power MOSFET. A MOSFET driver like the MCP1403/4/5 family can be used to provide additional source/sink current capability.

4.2 MOSFET Driver Timing

The ability of a MOSFET driver to transition from a fully off state to a fully on state are characterized by the drivers rise time (t_R), fall time (t_F), and propagation delays (t_{D1} and t_{D2}). The MCP1403/4/5 family of drivers can typically charge and discharge a 2200 pF load capacitance in 15 ns along with a typical matched propagation delay of 40 ns. Figure 4-1 and Figure 4-2 show the test circuit and timing waveform used to verify the MCP1403/4/5 timing.

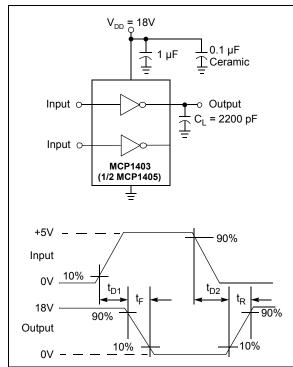


FIGURE 4-1: Inverting Driver Timing Waveform.

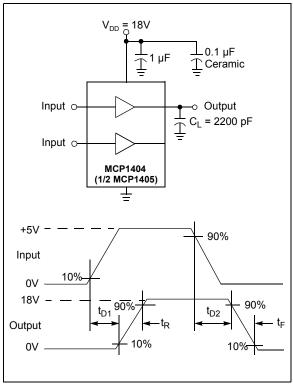


FIGURE 4-2: Non-Inverting Driver Timing Waveform.

4.3 Decoupling Capacitors

Careful layout and decoupling capacitors are highly recommended when using MOSFET drivers. Large currents are required to charge and discharge capacitive loads quickly. For example, 2.5A are needed to charge a 2200 pF load with 18V in 16 ns.

To operate the MOSFET driver over a wide frequency range with low supply impedance a ceramic and low ESR film capacitor are recommended to be placed in parallel between the driver V_{DD} and GND. A 1.0 μF low ESR film capacitor and a 0.1 μF ceramic capacitor placed between V_{DD} and GND pins should be used. These capacitors should be placed close to the driver to minimized circuit board parasitics and provide a local source for the required current.

4.4 PCB Layout Considerations

Proper PCB layout is important in a high current, fast switching circuit to provide proper device operation and robustness of design. PCB trace loop area and inductance should be minimized by the use of ground planes or trace under MOSFET gate drive signals, separate analog and power grounds, and local driver decoupling.

Placing a ground plane beneath the MCP1403/4/5 will help as a radiated noise shield as well as providing some heat sinking for power dissipated within the device.

4.5 Power Dissipation

The total internal power dissipation in a MOSFET driver is the summation of three separate power dissipation elements.

$$P_T = P_L + P_Q + P_{CC}$$

Where:

P_T = Total power dissipation

P_I = Load power dissipation

P_O = Quiescent power dissipation

P_{CC} = Operating power dissipation

4.5.1 CAPACITIVE LOAD DISSIPATION

The power dissipation caused by a capacitive load is a direct function of frequency, total capacitive load, and supply voltage. The power lost in the MOSFET driver for a complete charging and discharging cycle of a MOSFET is:

$$P_L = f \times C_T \times V_{DD}^{2}$$

Where:

f = Switching frequency

C_T = Total load capacitance

V_{DD} = MOSFET driver supply voltage

4.5.2 QUIESCENT POWER DISSIPATION

The power dissipation associated with the quiescent current draw depends upon the state of the input pin. The MCP1403/4/5 devices have a quiescent current draw when both inputs are high of 1.0 mA (typ) and 0.15 mA (typ) when both inputs are low. The quiescent power dissipation is:

$$P_{Q} = (I_{QH} \times D + I_{QL} \times (1 - D)) \times V_{DD}$$

Where:

 I_{QH} = Quiescent current in the high state

D = Duty cycle

I_{OL} = Quiescent current in the low state

V_{DD} = MOSFET driver supply voltage

4.5.3 OPERATING POWER DISSIPATION

The operating power dissipation occurs each time the MOSFET driver output transitions because for a very short period of time both MOSFETs in the output stage are on simultaneously. This cross-conduction current leads to a power dissipation describes as:

$$P_{CC} = CC \times f \times V_{DD}$$

Where:

CC = Cross-conduction constant (A*sec)

f = Switching frequency

V_{DD} = MOSFET driver supply voltage

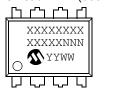
5.0 PACKAGING INFORMATION

5.1 Package Marking Information (Not to Scale)

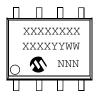
8-Lead DFN



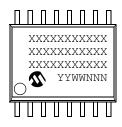
8-Lead PDIP (300 mil)



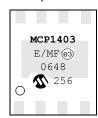
8-Lead SOIC (150 mil)



16-Lead SOIC (300 mil)



Example:



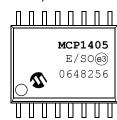
Example:



Example:



Example:



Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

(e3) Pb-free JEDEC designator for Matte Tin (Sn)

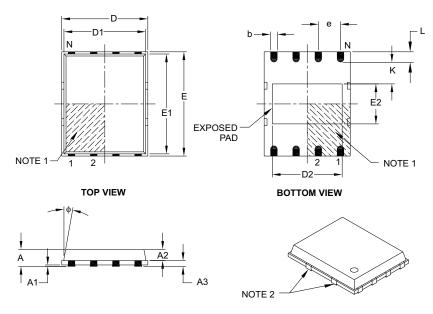
This package is Pb-free. The Pb-free JEDEC designator (e3) can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available

characters for customer-specific information.

8-Lead Plastic Dual Flat, No Lead Package (MF) – 6x5 mm Body [DFN-S] PUNCH SINGULATED

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units			MILLIMETERS			
	Dimension Limits	MIN	NOM	MAX			
Number of Pins	N		8				
Pitch	е		1.27 BSC				
Overall Height	Α	_	0.85	1.00			
Molded Package Thickness	A2	_	0.65	0.80			
Standoff	A1	0.00	0.01	0.05			
Base Thickness	A3	0.20 REF					
Overall Length	D	4.92 BSC					
Molded Package Length	D1		4.67 BSC				
Exposed Pad Length	D2	3.85 4.00 4.15					
Overall Width	E		5.99 BSC				
Molded Package Width	E1		5.74 BSC				
Exposed Pad Width	E2	2.16	2.31	2.46			
Contact Width	b	0.35 0.40 0.47					
Contact Length	L	0.50 0.60 0.75					
Contact-to-Exposed Pad	K	0.20 – –					
Model Draft Angle Top	ф	_	_	12°			

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package may have one or more exposed tie bars at ends.
- 3. Dimensioning and tolerancing per ASME Y14.5M.

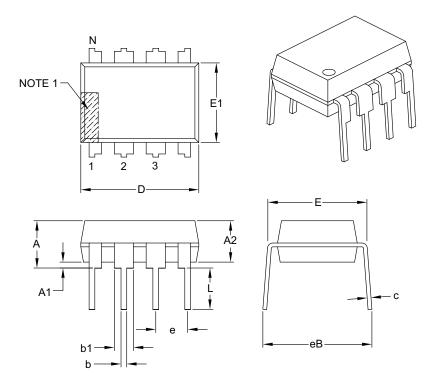
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-113B

8-Lead Plastic Dual In-Line (P) – 300 mil Body [PDIP]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	INCHES		
Dimension	n Limits	MIN	NOM	MAX
Number of Pins	N		8	
Pitch	е		.100 BSC	
Top to Seating Plane	Α	_	_	.210
Molded Package Thickness	A2	.115	.130	.195
Base to Seating Plane	A1	.015	_	_
Shoulder to Shoulder Width	Е	.290	.310	.325
Molded Package Width	E1	.240	.250	.280
Overall Length	D	.348	.365	.400
Tip to Seating Plane	L	.115	.130	.150
Lead Thickness	С	.008	.010	.015
Upper Lead Width	b1	.040	.060	.070
Lower Lead Width	b	.014	.018	.022
Overall Row Spacing §	eВ	_	_	.430

Notes:

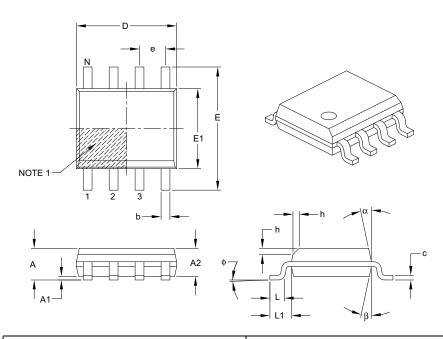
- 1. Pin 1 visual index feature may vary, but must be located with the hatched area.
- 2. \S Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .010" per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-018B

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS			
Dimension	Dimension Limits		NOM	MAX	
Number of Pins	N		8		
Pitch	е		1.27 BSC		
Overall Height	Α	ı	_	1.75	
Molded Package Thickness	A2	1.25	_	-	
Standoff §	A1	0.10	_	0.25	
Overall Width	Е	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	4.90 BSC			
Chamfer (optional)	h	0.25	_	0.50	
Foot Length	L	0.40	_	1.27	
Footprint	L1		1.04 REF		
Foot Angle	ф	0°	_	8°	
Lead Thickness	С	0.17 – 0.25			
Lead Width	b	0.31	_	0.51	
Mold Draft Angle Top	α	5°	_	15°	
Mold Draft Angle Bottom	β	5°	_	15°	

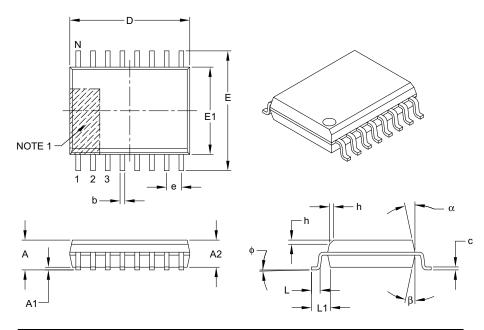
Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 - REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-057B

16-Lead Plastic Small Outline (SO) – Wide, 7.50 mm Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	Units	MILLIMETERS		
]	Dimension Limits	MIN	NOM	MAX
Number of Pins	N		16	
Pitch	е		1.27 BSC	
Overall Height	Α	ı	_	2.65
Molded Package Thickness	A2	2.05	_	_
Standoff §	A1	0.10	_	0.30
Overall Width	E	10.30 BSC		
Molded Package Width	E1	7.50 BSC		
Overall Length	D	10.30 BSC		
Chamfer (optional)	h	0.25 – 0.75		
Foot Length	L	0.40	_	1.27
Footprint	L1		1.40 REF	
Foot Angle	ф	0°	_	8°
Lead Thickness	С	0.20 – 0.33		
Lead Width	b	0.31	_	0.51
Mold Draft Angle Top	α	5°	_	15°
Mold Draft Angle Bottom	β	5°	_	15°

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic.
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M.

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-102B

APPENDIX A: REVISION HISTORY

Revision B (May 2007)

- Page 13: Updated Package Outline Drawing
- Page 14: Updated Package Outline Drawing
- Page 15: Updated Package Outline Drawing
- Page 16: Updated Package Outline Drawing
- Page 17: Updated Revision History
- Page 19: Corrected Package Codes in Product Identification System

Revision A (December 2006)

· Original Release of this Document.

MCP1403/4/5

NOTES:

PRODUCT IDENTIFICATION SYSTEM

 $\label{thm:condition} \mbox{To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales of fice.}$

PART NO. X	<u> </u>	Exa	imples:	
Device Tempe Ran	•	a)	MCP1403-E/SN:	4.5A Dual Inverting MOSFET Driver, 8LD SOIC package.
Device:	MCP1403: 4.5A Dual MOSFET Driver, Inverting MCP1403T: 4.5A Dual MOSFET Driver, Inverting	b)	MCP1403-E/P:	4.5A Dual Inverting MOSFET Driver, 8LD PDIP package.
(Tape and Reel) MCP1404: 4.5A Dual MOSFET Driver, Non-Inverting MCP1404T: 4.5A Dual MOSFET Driver, Non-Inverting (Tape and Reel) MCP1405: 4.5A Dual MOSFET Driver, Complementary MCP1405T: 4.5A Dual MOSFET Driver, Complementary (Tape and Reel)	c)	MCP1403-E/MF:	4.5A Dual Inverting MOSFET Driver, 8LD DFN package.	
	d)	MCP1403-E/SO:	4.5A Dual InvertingMOSFET Driver,16LD SOIC package.	
Temperature Range:	E = -40°C to +125°C	a)	MCP1404T-E/SN:	4.5A Dual Non-Inverting, MOSFET Driver,
Package: *	MF = Dual, Flat, No-Lead (6x5 mm Body), 8-lead P = Plastic DIP, (300 mil body), 8-lead SN = Plastic SOIC (150 mil Body), 8-Lead SO = Plastic SOIC (Wide), 16-Lead	b)	MCP1404-E/P:	8LD SOIC package, 4.5A Dual Non-Inverting, MOSFET Driver, 8LD PDIP package.
	* All package offerings are Pb Free (Lead Free)	a)	MCP1405-E/SN:	4.5A Dual Complementary,MOSFET Driver,8LD SOIC package.
		b)	MCP1405-E/P:	4.5A Dual Complementary, MOSFET Driver, 8LD PDIP package.
		c)	MCP1405T-E/SO	Tape and Reel, 4.5A Dual Complementary MOSFET Driver, 16LD SOIC package.

MCP1403/4/5

NOTES:

Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
 knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
 Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, Accuron, dsPIC, KEELOQ, KEELOQ logo, microID, MPLAB, PIC, PICmicro, PICSTART, PRO MATE, rfPIC and SmartShunt are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AmpLab, FilterLab, Linear Active Thermistor, Migratable Memory, MXDEV, MXLAB, SEEVAL, SmartSensor and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, CodeGuard, dsPICDEM, dsPICDEM.net, dsPICworks, ECAN, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, Mindi, MiWi, MPASM, MPLAB Certified logo, MPLIB, MPLINK, PICkit, PICDEM, PICDEM.net, PICLAB, PICtail, PowerCal, PowerInfo, PowerMate, PowerTool, REAL ICE, rfLAB, Select Mode, Smart Serial, SmartTel, Total Endurance, UNI/O, WiperLock and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2007, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

QUALITY MANAGEMENT SYSTEM

CERTIFIED BY DNV

ISO/TS 16949:2002

Microchip received ISO/TS-16949:2002 certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona; Gresham, Oregon and design centers in California and India. The Company's quality system processes and procedures are for its PIC® MCUs and dsPIC® DSCs, KEELOQ® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office 2355 West Chandler Blvd.

Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277

Technical Support:

http://support.microchip.com

Web Address: www.microchip.com

Atlanta

Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455

Roston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

Kokomo, IN Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

Santa Clara

Santa Clara, CA Tel: 408-961-6444 Fax: 408-961-6445

Toronto

Mississauga, Ontario, Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Asia Pacific Office

Suites 3707-14, 37th Floor Tower 6, The Gateway Habour City, Kowloon Hong Kong

Tel: 852-2401-1200 Fax: 852-2401-3431

Australia - Sydney Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing

Tel: 86-10-8528-2100 Fax: 86-10-8528-2104

China - Chengdu Tel: 86-28-8665-5511 Fax: 86-28-8665-7889

China - Fuzhou

Tel: 86-591-8750-3506 Fax: 86-591-8750-3521

China - Hong Kong SAR Tel: 852-2401-1200

Fax: 852-2401-3431 China - Qingdao

Tel: 86-532-8502-7355 Fax: 86-532-8502-7205

China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066

China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Shunde

Tel: 86-757-2839-5507 Fax: 86-757-2839-5571

China - Wuhan

Tel: 86-27-5980-5300 Fax: 86-27-5980-5118

China - Xian

Tel: 86-29-8833-7250 Fax: 86-29-8833-7256

ASIA/PACIFIC

India - Bangalore

Tel: 91-80-4182-8400 Fax: 91-80-4182-8422

India - New Delhi

Tel: 91-11-4160-8631 Fax: 91-11-4160-8632

India - Pune

Tel: 91-20-2566-1512 Fax: 91-20-2566-1513

Japan - Yokohama Tel: 81-45-471- 6166

Fax: 81-45-471-6122

Korea - Gumi

Tel: 82-54-473-4301 Fax: 82-54-473-4302

Korea - Seoul

Tel: 82-2-554-7200 Fax: 82-2-558-5932 or 82-2-558-5934

Malaysia - Penang Tel: 60-4-646-8870

Fax: 60-4-646-5086

Philippines - Manila

Tel: 63-2-634-9065 Fax: 63-2-634-9069

Singapore Tel: 65-6334-8870

Fax: 65-6334-8850 Taiwan - Hsin Chu

Tel: 886-3-572-9526 Fax: 886-3-572-6459

Taiwan - Kaohsiung

Tel: 886-7-536-4818 Fax: 886-7-536-4803

Taiwan - Taipei

Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Thailand - Bangkok Tel: 66-2-694-1351

Fax: 66-2-694-1350

EUROPE

Austria - Wels

Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 Denmark - Copenhagen

Tel: 45-4450-2828 Fax: 45-4485-2829

France - Paris

Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Munich

Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan

Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen

Tel: 31-416-690399 Fax: 31-416-690340

Spain - Madrid Tel: 34-91-708-08-90

Fax: 34-91-708-08-91 UK - Wokingham

Tel: 44-118-921-5869 Fax: 44-118-921-5820

12/08/06